Transport Properties of Ramp-edge Junction with Columnar Defects

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We have investigated the transport properties in YBa₂Cu₃O_{7-x} (YBCO) ramp-edge junctions fabricated with 2 and 5 μ m width that are irradiated by heavy ion-beam. We observed that RSJ-like behavior in the range from 40K to 60K and the normal state junction resistance (R_n) was almost constant of temperature. From the linear dependence of critical current (I_c) on temperature, the junctions seem likely to behave as SIS (Superconductor-Insulator-Superconductor) type junction. Noise measurement showed that I_c fluctuation peak increases with increasing temperature, whereas R_n fluctuation remains almost constant. Comparing with the model I_c and R_n fluctuations are seemed to be antiphase correlated and I_cR_n ~ J_c^q with 0.4 < q < 0.8.

keywords: ramp-edge junction, noise, Josephson junction, multilayers